

Features

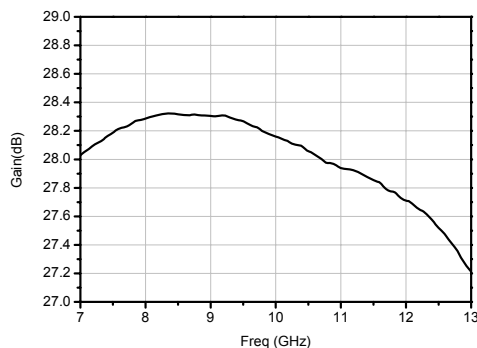
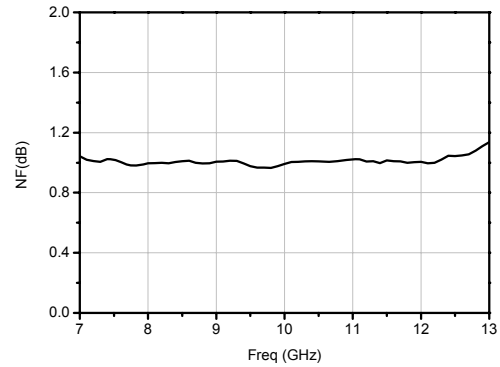
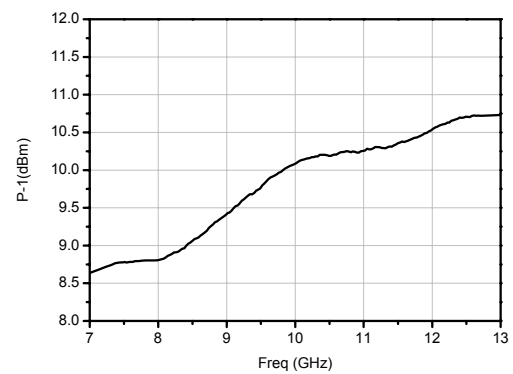
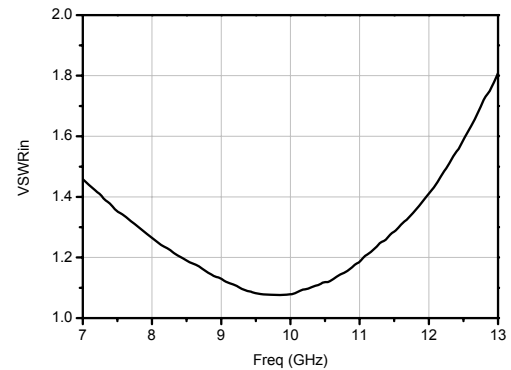
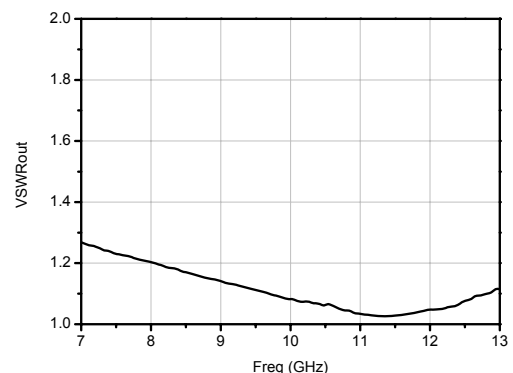
- Freq: 8~12GHz
- Gain: 28dB
- Noise Figure: 1dB
- Output Power for 1 dB Compression: 10dBm
- Supply Voltage: +5V
- Supply Current: 40mA
- Chip Size: 1.8mm×0.85mm×0.1mm

General Description

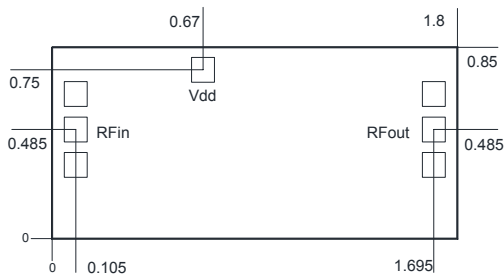
The HG115FN is a GaAs pHEMT MMIC Low Noise Amplifier operating between 8 and 12GHz. The LNA has been optimized to provide 28dB gain, 1dB noise figure and 10 dBm output power for 1dB compression.

Electrical Specifications ($T_A=25^\circ\text{C}$, $V_{dd}=+5\text{V}$).

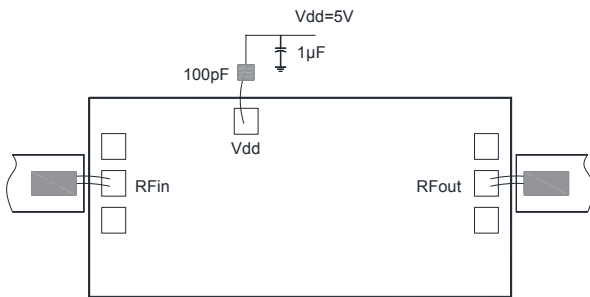
Parameter	Min.	Typ.	Max.
Freq(GHz)	8~12		
Gain (dB)	—	28	—
Gain Flatness (dB)	—	± 0.5	—
Input VSWR	—	1.4	—
Output VSWR	—	1.2	—
Noise Figure(dB)	—	1	—
Output Power for 1 dB Compression(dBm)	—	10	—

Measured Performance
Gain

Noise Figure

Output Power for 1dB Compression

Input VSWR

Output VSWR


Outline Drawing (mm)



Assembly Diagram



Absolute Maximum Ratings

Supply Voltage	+5.5V
RF Input Power	+18dBm
Operating Temperature	-55°C ~ 125°C
Storage Temperature	-65°C ~ 150°C

Notes:

1. The chip should be stored in a dry and nitrogen environment, and used in a clean environment.
2. GaAs material is brittle, can not touch the surface of the chip, must be careful when using.
3. The chip is welding with conductive adhesive or alloy (alloy temperature should not exceed 300°C, and no more than 30 sec.), and should make it fully grounded.
4. The chip microwave port and substrate gap is not exceeding 0.05mm, with $\Phi 25\mu\text{m}$ double gold wire bonding, suggested length of gold wire 250~400 μm .
5. Chip microwave port with a DC blocking capacitor.
6. The chip is sensitive to static electricity, and should be protected against static electricity during storage and use.